We claim:

1. A ternary-form system of polysilicon suitable for manufacture of silicon ingots, which system comprises a first component (Component A) being polysilicon in a rod form; a second component (Component B) being polysilicon in a chunk form; and a third component (Component C) being polysilicon in a granule form, wherein Component A is present in an amount of from 10 to 60 weight percent, Component B is present in an amount of from 10 to 60 weight percent, Component C is present in an amount of from 20 to 70 weight percent and the percentage amounts of Component A, Component B and Component C as present do not exceed a total of 100 percent.

~~2. The system of Claim 1 wherein Component A is present in an amount of from 10 to 80 weight percent based on total weight of the system.~~

~~3. The system of Claim 1 wherein Component B is present in an amount of from 10 to 80 weight percent based on total weight of the system.~~

~~4. The system of Claim 1 wherein Component C is present in an amount of from 10 to 80 weight percent based on total weight of the system.~~

~~5. The system of Claim 1 where in Component A is present in an amount of from 10 to 60 weight percent; Component B is present in an amount of from 10 to 60 weight percent; and Component C is present in an amount of from 20 to 70 weight percent; and wherein the percentage amounts of Component A, Component B and Component C as present do not exceed a total of 100 percent.~~

~~6.~~2. The system of Claim ~~5~~1 wherein:
Component A is present in an amount of from 30 to 50 weight percent;
Component B is present in an amount of from 10 to 40 weight percent; ~~and~~
Component C is present in an amount of from 20 to 60 weight percent; and ~~wherein~~
the percentage amounts of Component A, Component B and Component C as present do not exceed a total of 100 percent.

~~7.~~3. The system of Claim 1 wherein Component A, the rod-form polysilicon, is rod-form polysilicon that was prepared by a Siemens Process.

~~8.~~4. The system of Claim 1 wherein Component B, the chunk-form polysilicon, is chunk-form polysilicon that was prepared by a Siemens process.

~~9.~~5. The system of Claim 1 wherein Component C, the granule-form polysilicon, is granule-form polysilicon that was prepared by a fluidized-bed process.

~~10.~~6. A directional solidification process for multicrystalline silicon, which process comprises:

providing a mold suitable for melting and cooling polysilicon using a directional solidification process;

loading a ternary-form system of polysilicon into the mold; ~~and~~

placing the mold into a furnace suitable for melting and cooling polysilicon by the directional solidification process;

heating the mold until polysilicon attains a desired state of molten silicon mass; and

cooling the mold thereby causing the molten silicon mass to crystallize and form a crystalline silicon ingot characterized in that the ternary-form system of polysilicon comprises a first component (Component A) being polysilicon in a rod form; a second component (Component B) being polysilicon in a chunk form; and a third component (Component C) being polysilicon in a granule form,

wherein Component A is present in an amount of from 10 to 60 weight percent, Component B is present in an amount of from 10 to 60 weight percent, Component C is present in an amount of from 20 to 70 weight percent, and the percentage amounts of Component A, Component B and Component C as present do not exceed a total of 100 percent.

~~11. The process of Claim 10 wherein Component A is present in an amount of from 10 to 80 weight percent based on total weight of the system.~~

~~12. The process of Claim 10 wherein Component B is present in an amount of from 10 to 80 weight percent based on total weight of the system.~~

~~13. The process of Claim 10 wherein Component C is present in an amount of from 10 to 80 weight percent based on total weight of the system.~~

~~14. The process of Claim 10 where in Component A is present in an amount of from 10 to 60 weight percent; Component B is present in an amount of from 10 to 60 weight percent; and Component C is present in an amount of from 20 to 70 weight percent; and wherein the percentage amounts of Component A, Component B and Component C as present do not exceed a total of 100 percent.~~

~~15.~~7. The ~~system~~ process of Claim ~~14~~ 6 wherein

Component A is present in an amount of from 30 to 50 weight percent;

Component B is present in an amount of from 10 to 40 weight percent; ~~and~~

Component C is present in an amount of from 20 to 60 weight percent; and ~~wherein~~

the percentage amounts of Component A, Component B and Component C as present do not exceed a total of 100 percent.

~~16.~~8. The process of Claim ~~10~~ 6 wherein Component A, the rod-form polysilicon, is rod-form polysilicon that was prepared by a Siemens Process.

~~17.~~9. The ~~system~~ process of Claim ~~10~~ 6 wherein Component B, the chunk-form polysilicon, is chunk-form polysilicon that was prepared by a Siemens process.

~~18.~~10. The process of Claim ~~10~~ 6 wherein Component C, the granule-form polysilicon, is granule-form polysilicon that was prepared by a fluidized-bed process.

~~19.~~11. A Czochralski process for the production of single crystal silicon, which process comprises:

providing a mold suitable for melting polysilicon;

loading a ternary-form system of polysilicon into the mold;

heating the mold until the polysilicon attains a desired state of molten silicon mass;

introducing a silicon seed crystal; and

pulling a single silicon crystal characterized in that the ternary-form system of polysilicon comprises a first component (Component A) being polysilicon in a rod form; a second component (Component B) being a polysilicon in a chunk form; and a third component (Component C) being polysilicon in a granule form,

wherein Component A is present in an amount of from 10 to 60 weight percent, Component B is present in an amount of from 10 to 60 weight percent, Component C is present in an amount of from 20 to 70 weight percent, and the percentage amounts of Component A, Component B and Component C as present do not exceed a total of 100 percent.

~~20. The process of Claim 19 wherein Component A is present in an amount of from 10 to 80 weight percent based on total weight of the system.~~

~~21. The process of Claim 19 wherein Component B is present in an amount of from 10 to 80 weight percent based on total weight of the system.~~

~~22. The process of Claim 19 wherein Component C is present in an amount of from 10 to 80 weight percent based on total weight of the system.~~

~~23. The process of Claim 19 where in Component A is present in an amount of from 10 to 60 weight percent; Component B is present in an amount of from 10 to 60 weight percent; and Component C is present in an amount of from 20 to 70 weight percent; and wherein the percentage amounts of~~

~~Component A, Component B and Component C as present do not exceed a total of 100 percent.~~

~~24.~~12. The ~~system~~ process of Claim ~~23~~ 11 wherein

Component A is present in an amount of from 30 to 50 weight percent;

Component B is present in an amount of from 10 to 40 weight percent; ~~and~~

Component C is present in an amount of from 20 to 60 weight percent; and ~~wherein~~

the percentage amounts of Component A, Component B and Component C as present do not exceed a total of 100 percent.

~~25.~~13. The process of Claim ~~19~~ 11 wherein Component A, the rod-form polysilicon, is rod-form polysilicon that was prepared by a Siemens Process.

~~26.~~14. The ~~system~~ process of Claim ~~19~~ 11 wherein Component B, the chunk-form polysilicon, is chunk-form polysilicon that was prepared by a Siemens process.

~~27.~~15. The process of Claim ~~19~~ 11 wherein Component C, the granule-form polysilicon, is granule-form polysilicon that was prepared by a fluidized-bed process.